

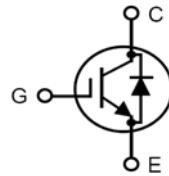
XPT™ 650V IGBT
GenX3™ w/Diode
IXYP10N65B3D1

$$V_{CES} = 650V$$

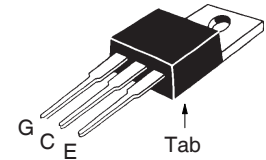
$$I_{C110} = 10A$$

$$V_{CE(sat)} \leq 1.95V$$

$$t_{fi(typ)} = 30ns$$

 Extreme Light Punch Through
 IGBT for 5-30kHz Switching


TO-220


 G = Gate C = Collector
 E = Emitter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	650	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	32	A
I_{C110}	$T_C = 110^\circ C$	10	A
I_{F110}	$T_C = 110^\circ C$	9	A
I_{CM}	$T_C = 25^\circ C$, 1ms	62	A
I_A	$T_C = 25^\circ C$	5	A
E_{AS}	$T_C = 25^\circ C$	50	mJ
SSOA	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 50\Omega$	$I_{CM} = 20$	A
(RBSOA)	Clamped Inductive Load	@ $V_{CE} \leq V_{CES}$	
t_{sc}	$V_{GE} = 15V$, $V_{CE} = 400V$, $T_J = 150^\circ C$	5	μs
(SCSOA)	$R_G = 150\Omega$, Non Repetitive		
P_C	$T_C = 25^\circ C$	160	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		2.5	g

Features

- Optimized for 5-30kHz Switching
- Square RBSOA
- Avalanche Rated
- Anti-Parallel Fast Diode
- Short Circuit Capability
- International Standard Package

Advantages

- High Power Density
- Extremely Rugged
- Low Gate Drive Requirement

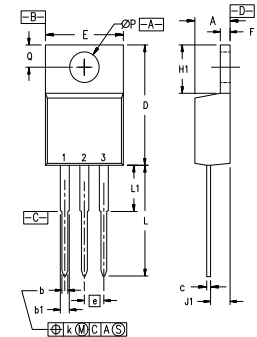
Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- High Frequency Power Inverters

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$			10 μA 350 μA $T_J = 150^\circ C$
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 10A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$		1.74 2.00	1.95 V V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 10\text{A}, V_{CE} = 10\text{V}$, Note 1	4.0	6.8	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		415	pF
C_{oes}			43	pF
C_{res}			10	pF
$Q_{g(on)}$	$I_C = 10\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		20	nC
Q_{ge}			3	nC
Q_{gc}			8	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 10\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 50\Omega$ Note 2		17	ns
t_{ri}			29	ns
E_{on}			0.30	mJ
$t_{d(off)}$			125	ns
t_{fi}			30	ns
E_{off}			0.20	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 10\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 50\Omega$ Note 2		19	ns
t_{ri}			35	ns
E_{on}			0.60	mJ
$t_{d(off)}$			147	ns
t_{fi}			116	ns
E_{off}			0.36	mJ
R_{thJC}			0.94	$^\circ\text{C/W}$
R_{thCS}		0.50		$^\circ\text{C/W}$

TO-220 Outline



Pins: 1 - Gate 2 - Collector
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
$\varnothing P$.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Reverse Diode (FRED)

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 10\text{A}, V_{GE} = 0\text{V}$, Note 1 $T_J = 150^\circ\text{C}$		1.6	3.0 V
I_{RM}	$I_F = 10\text{A}, V_{GE} = 0\text{V},$ $-di_F/dt = 200\text{A}/\mu\text{s}, V_R = 100\text{V}, T_J = 150^\circ\text{C}$		6.3	A
t_{rr}			170	ns
R_{thJC}				2.30 $^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

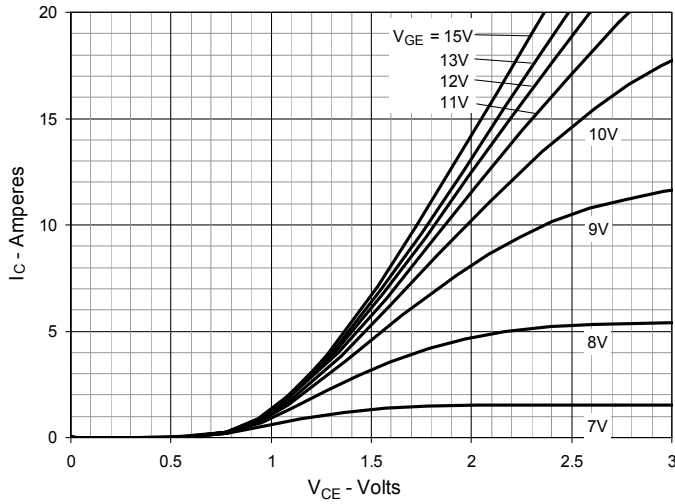


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

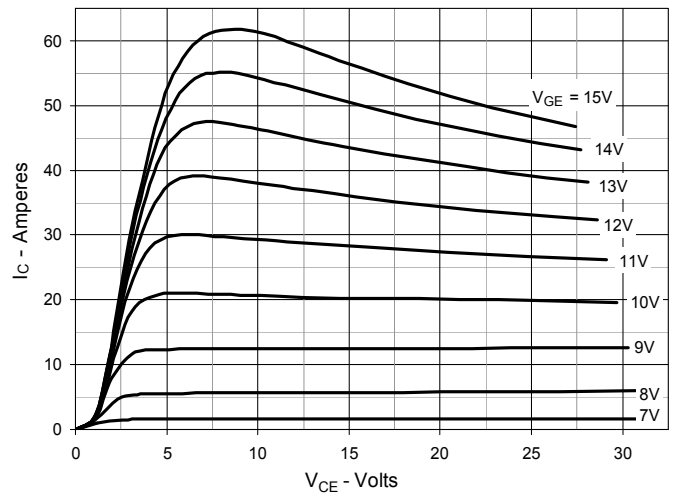


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

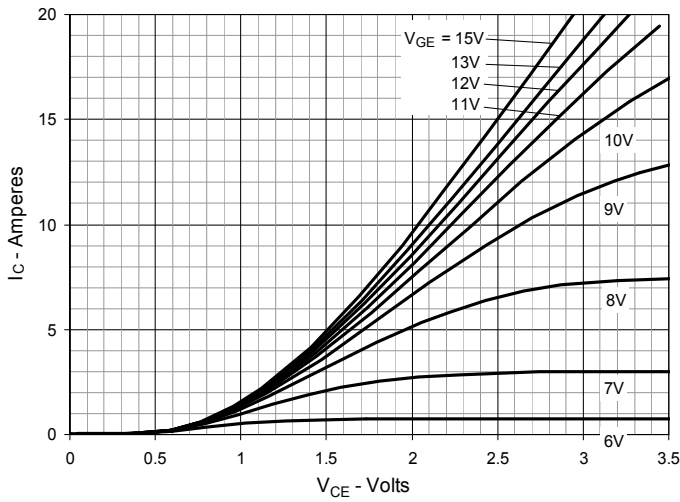


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

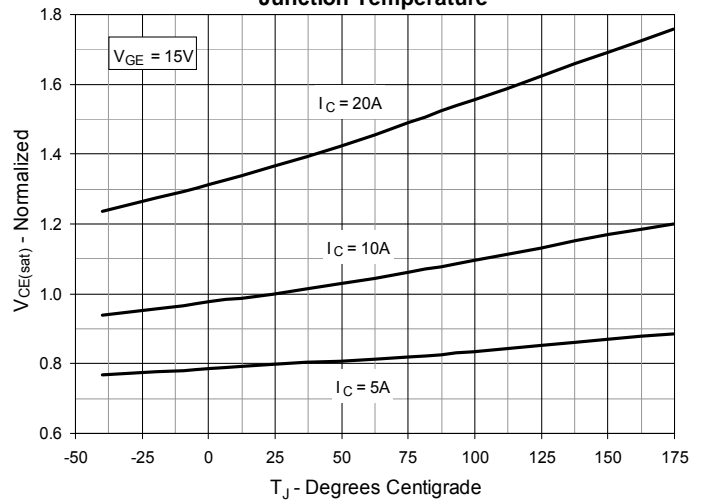


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

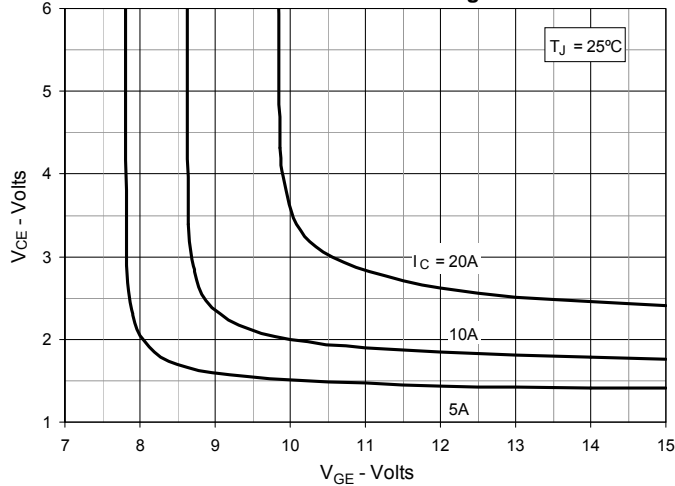


Fig. 6. Input Admittance

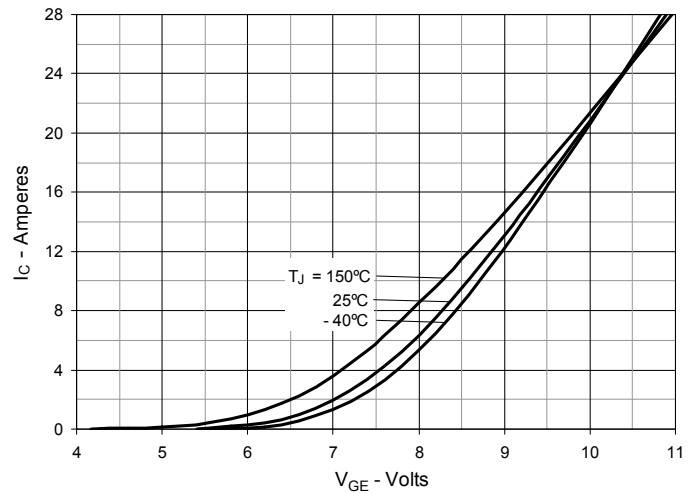


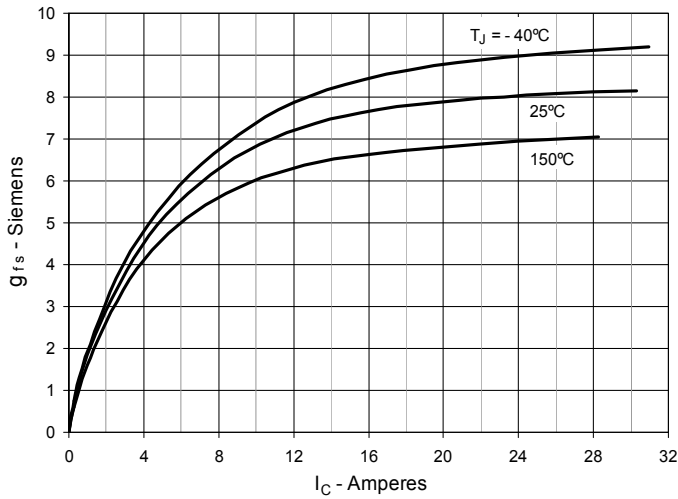
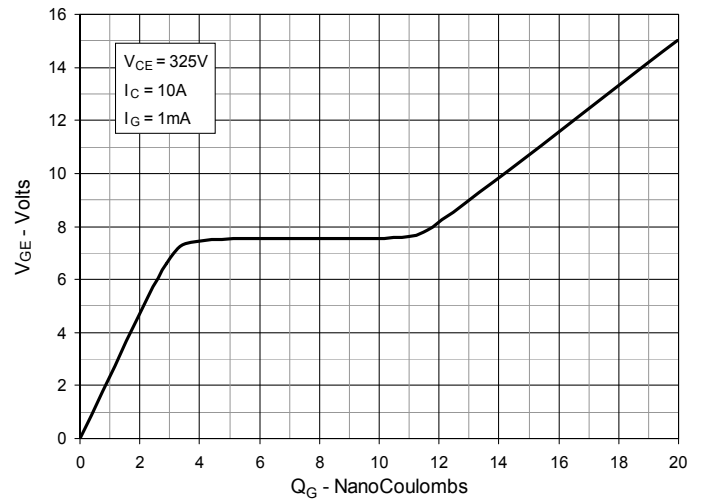
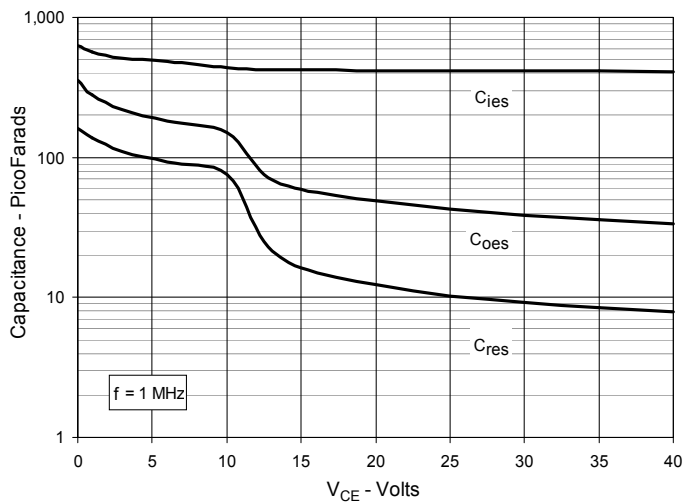
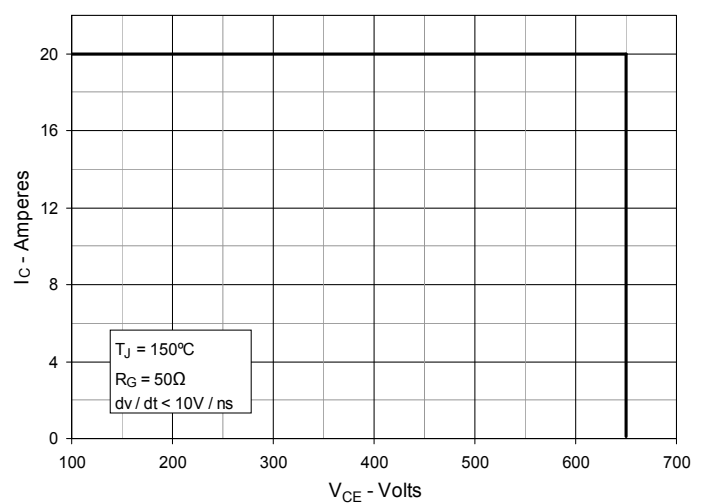
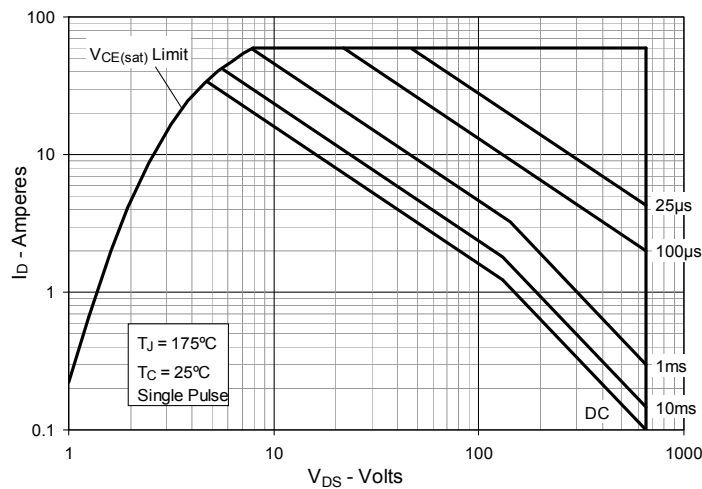
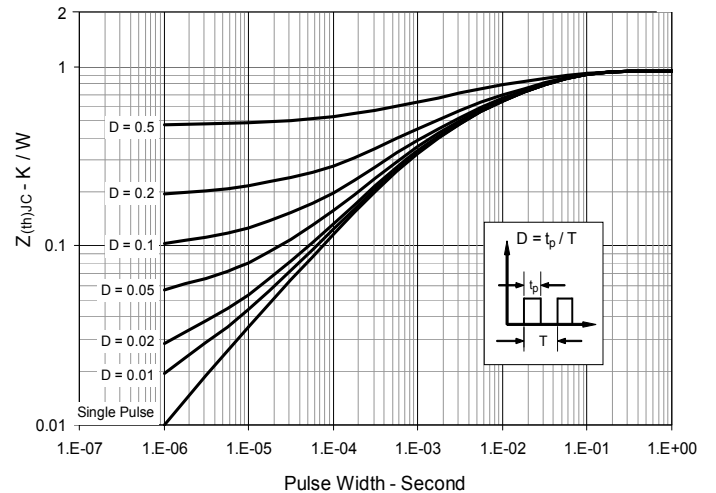
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Forward-Bias Safe Operating Area

Fig. 12. Maximum Transient Thermal Impedance (IGBT)


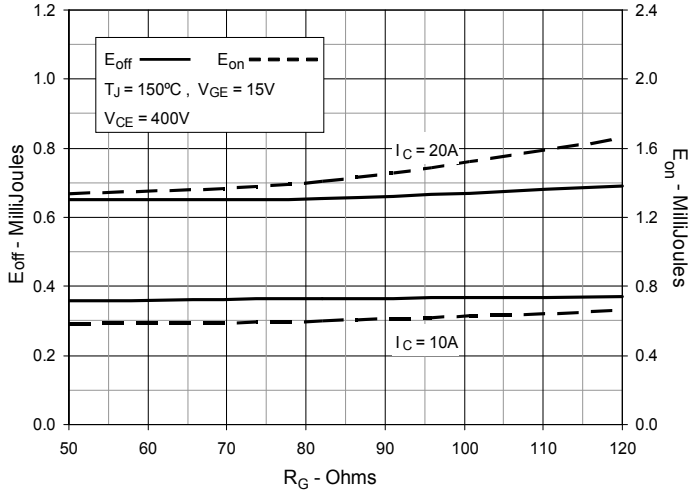
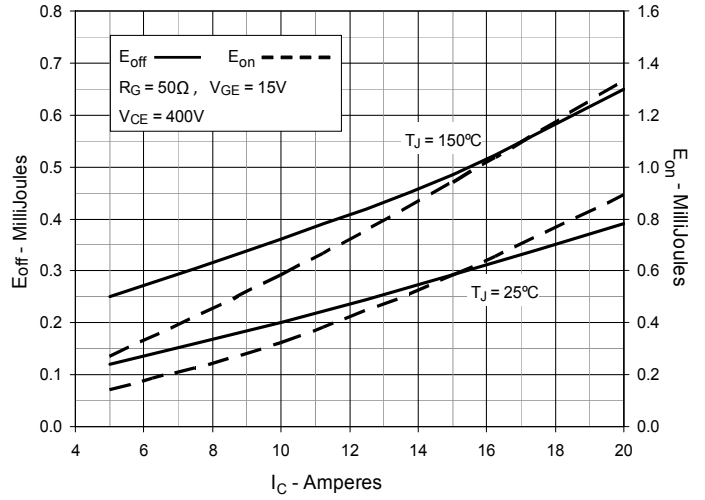
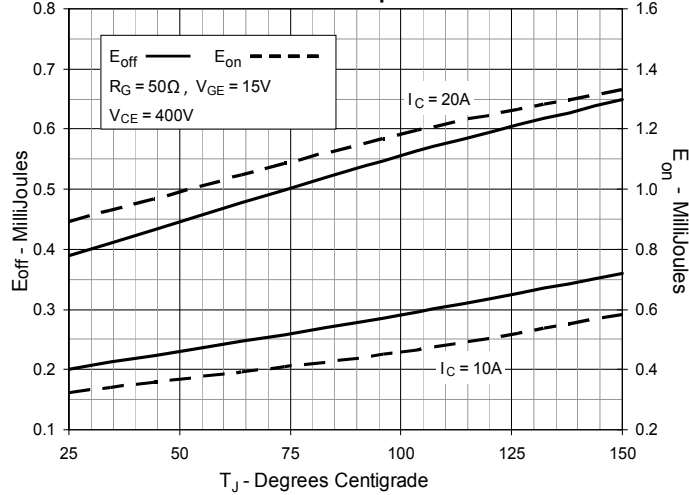
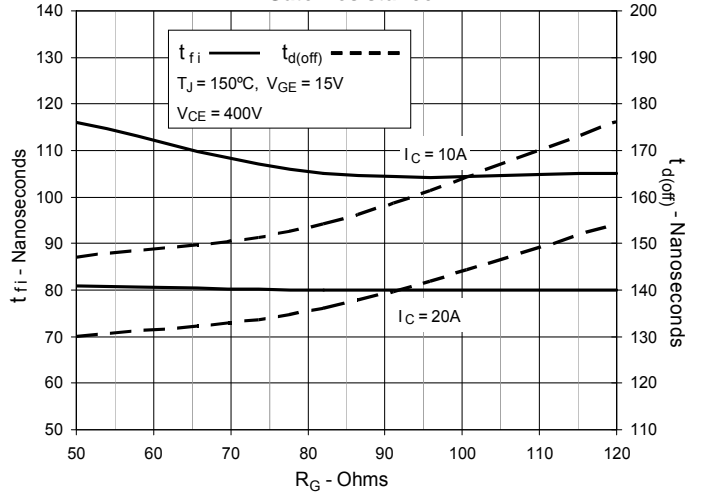
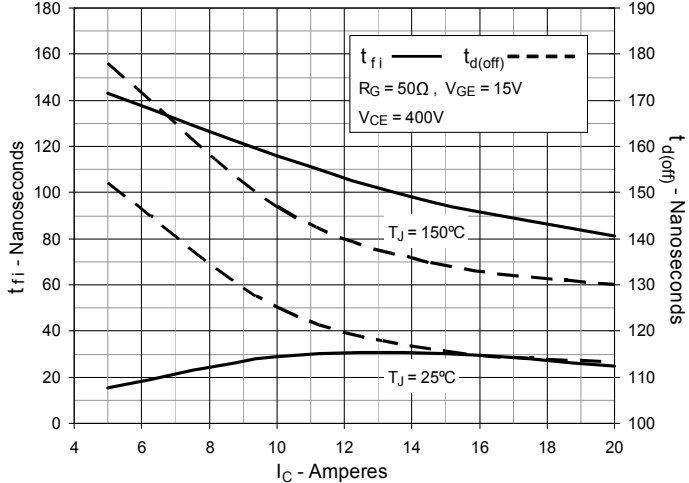
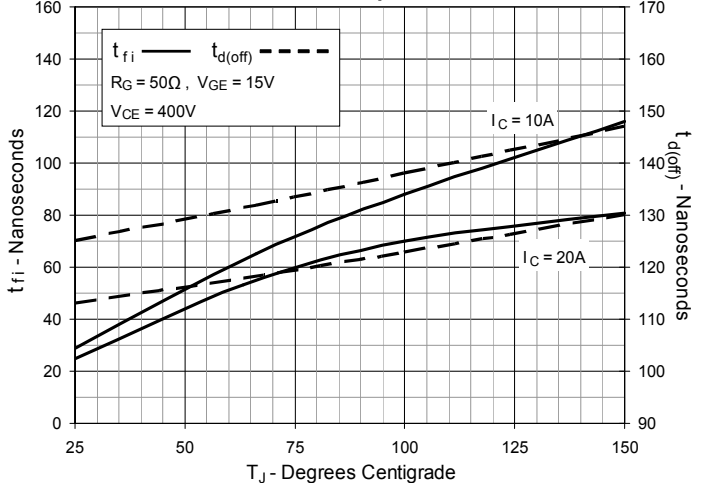
Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 14. Inductive Switching Energy Loss vs. Collector Current

Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

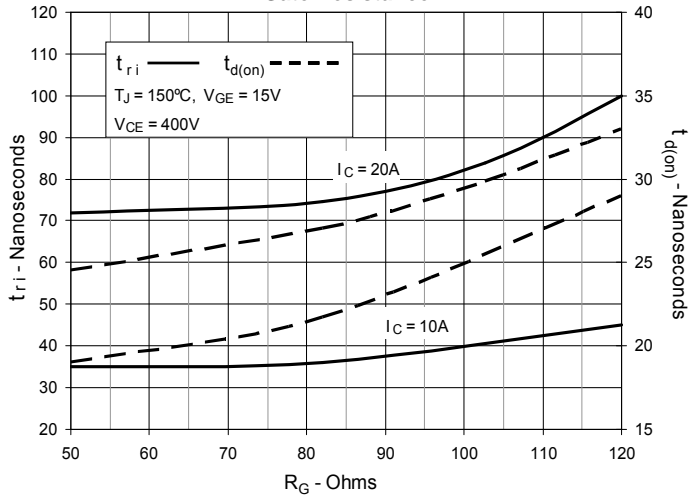


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

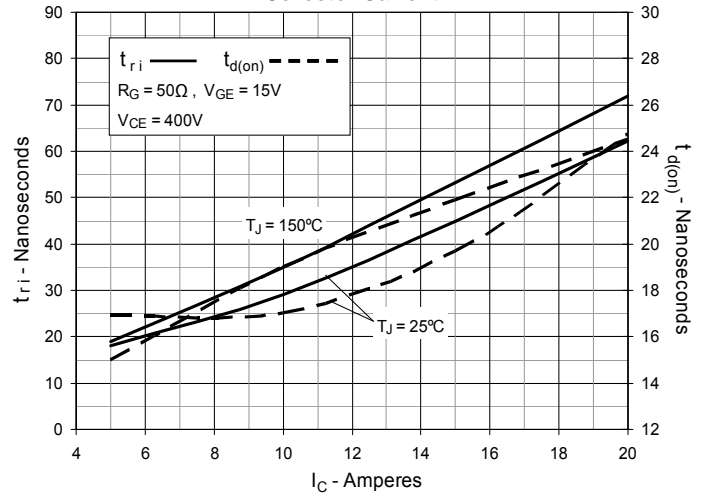


Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature

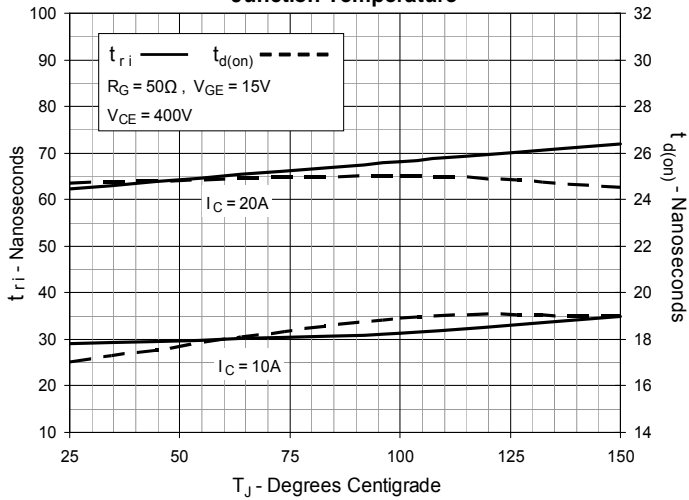
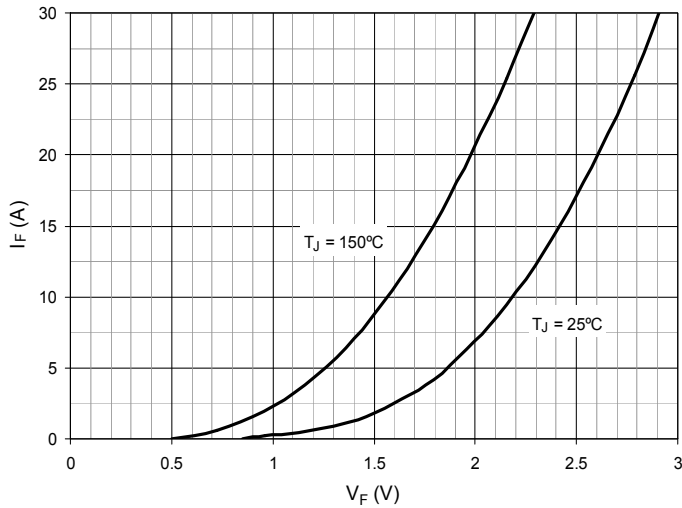
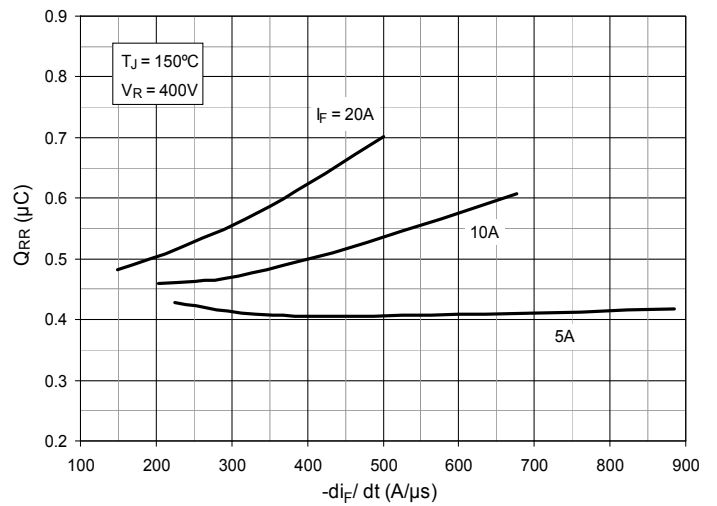
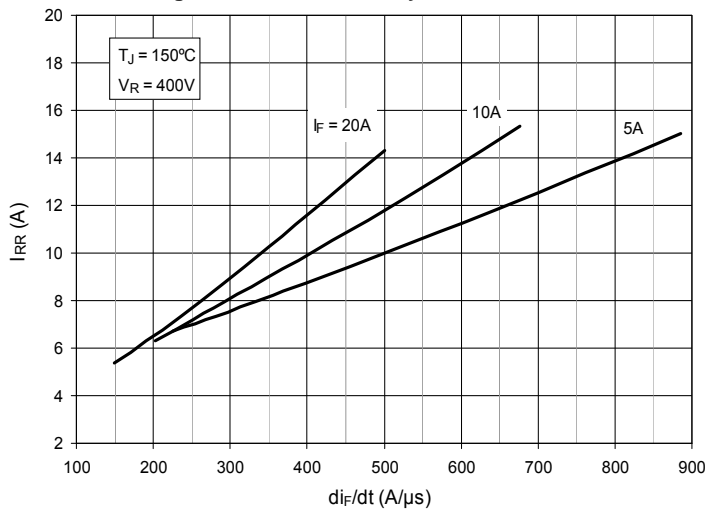
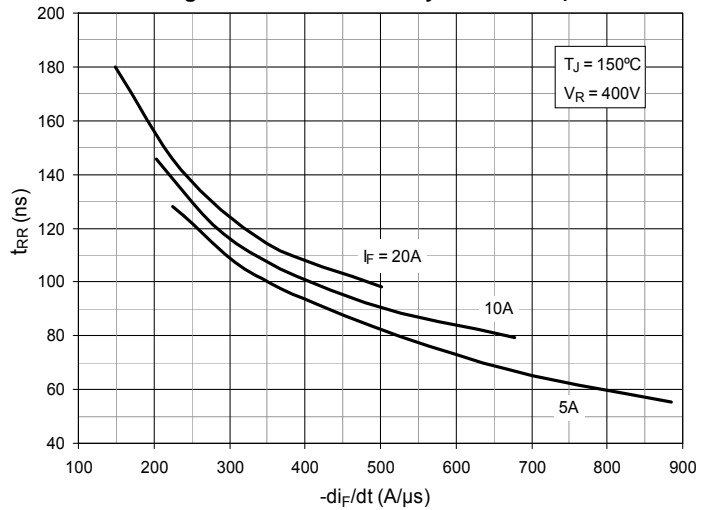
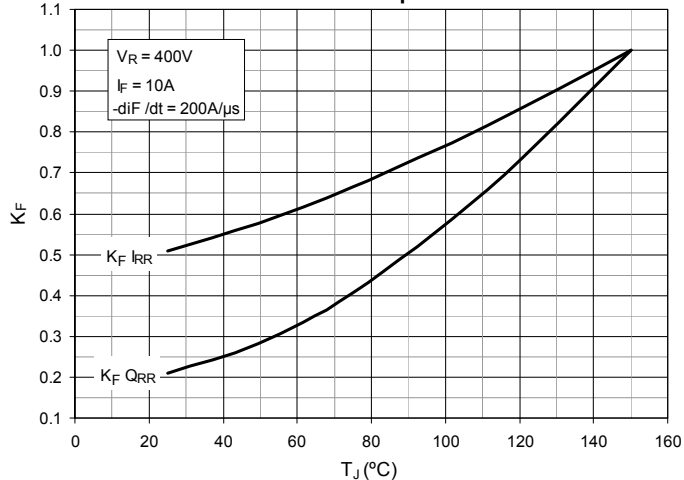
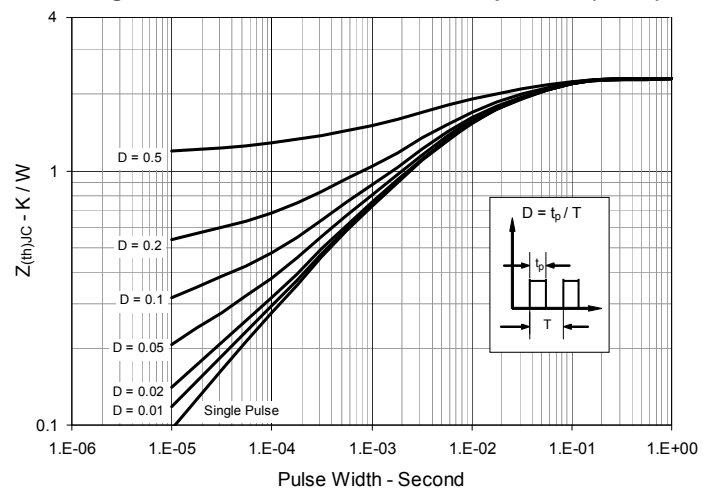


Fig. 22. Diode Forward Characteristics

Fig. 23. Reverse Recovery Charge vs. $-di_F/dt$

Fig. 24 Reverse Recovery Current vs. $-di_F/dt$

Fig. 25. Reverse Recovery Time vs. $-di_F/dt$

Fig. 26. Dynamic Parameters Q_{RR} , I_{RR} vs. Junction Temperature

Fig. 27. Maximum Transient Thermal Impedance (Diode)




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